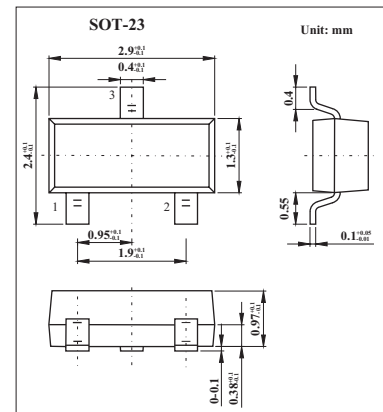


Silicon Schottky Diode

BAT68;BAT68-04
BAT68-05;BAT68-06

■ Features

- For mixer applications in VHF/UHF range
- For high-speed switching application



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	8	V
Forward current	I _F	130	mA
Total power dissipation BAT68, T _s ≤ 77 °C BAT68-04, BAT68-06, T _s ≤ 61 °C BAT68-05, T _s ≤ 46 °C	P _{tot}	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Junction - soldering point(Note 1)			
BAT68	R _{thJS}	≤ 490	K/W
BAT68-04, BAT68-06		≤ 590	
BAT68-05		≤ 690	

Note

1. For calculation of R_{thJA} please refer to Application Note Thermal Resistance

BAT68;BAT68-04 BAT68-05;BAT68-06

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)} = 10 \mu\text{A}$	8			V
Reverse current	I_R	$V_R = 1\text{V}$			0.1	μA
		$V_R = 1\text{V}, T_A = 60^\circ\text{C}$			1.2	
Forward voltage	V_F	$I_F = 1\text{mA}$		318	340	mV
		$I_F = 10\text{mA}$	340	390	500	
Diode capacitance	C_T	$V_R = 0, f = 1\text{MHz}$			1	pF
Differential forward resistance	R_F	$I_F = 5\text{mA}, f = 10\text{kHz}$			10	Ω

■ Marking

Type	BAT68	BAT68-04	BAT68-05	BAT68-06
Marking	83s	84s	85s	86s